

Initial Results in Semiconductor Manufacturing Plasmas

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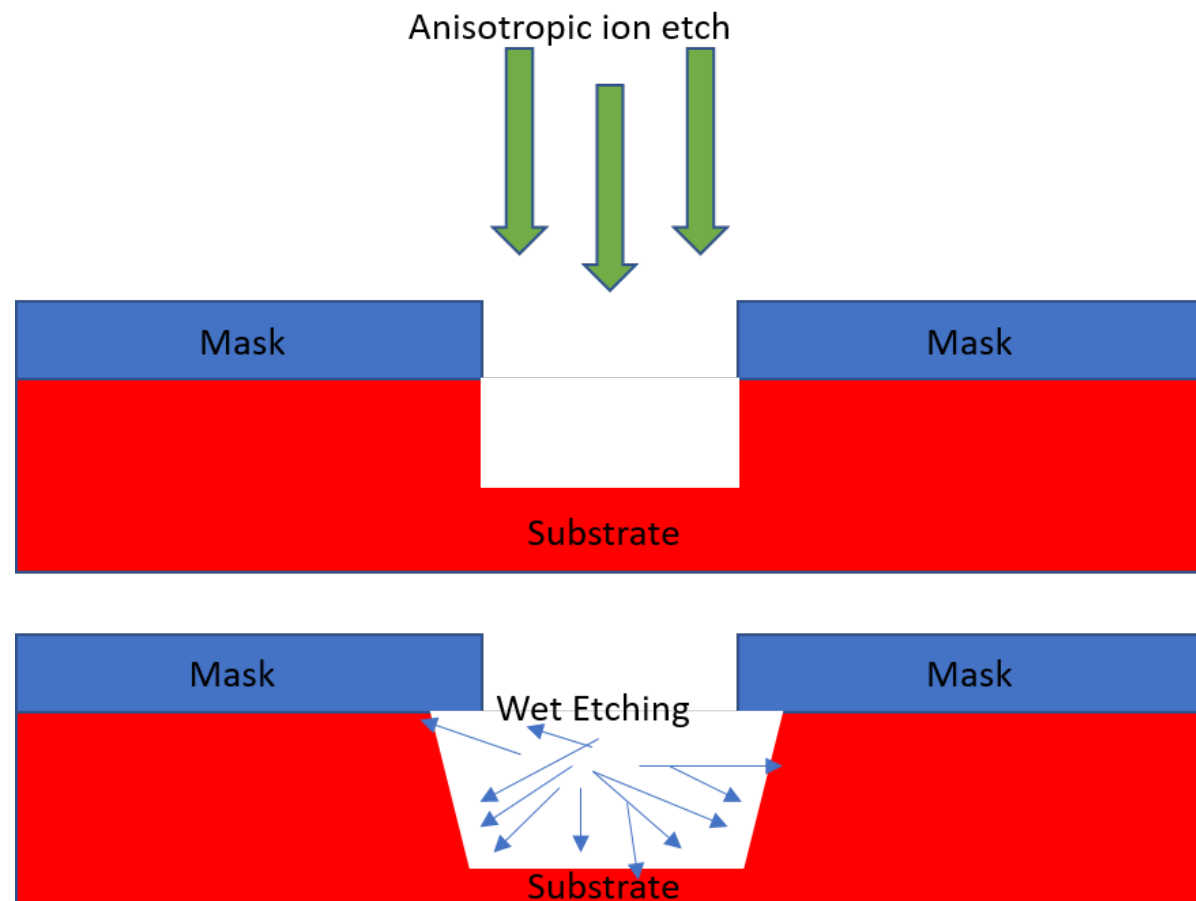
16 August 2018

Princeton Plasma Physics Lab – Graduate Summer School



Industry Plasmas

- Plasma is used for semiconductor etching and doping.
- Provides more controllable, anisotropic etches compared with “wet” etching.
- Much more green, no need for harmful chemicals



Moore's Law

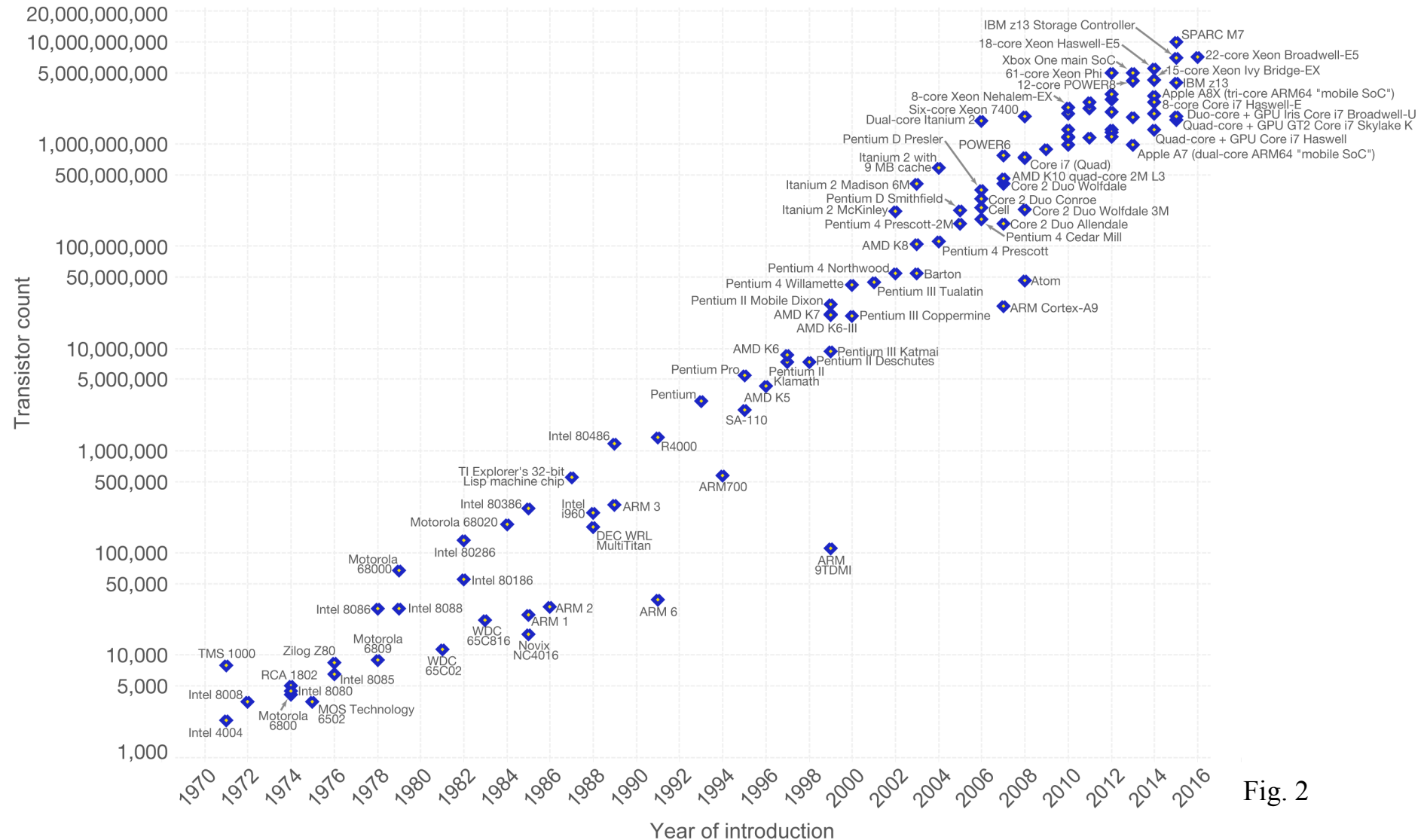


Fig. 2

Transistors

- Semiconductor features are reaching the nanoscale
- Silicon atoms are $\sim 0.2\text{nm}$ in diameter
 - We are reaching a natural limitation
- Smallest defect will greatly affect overall performance.

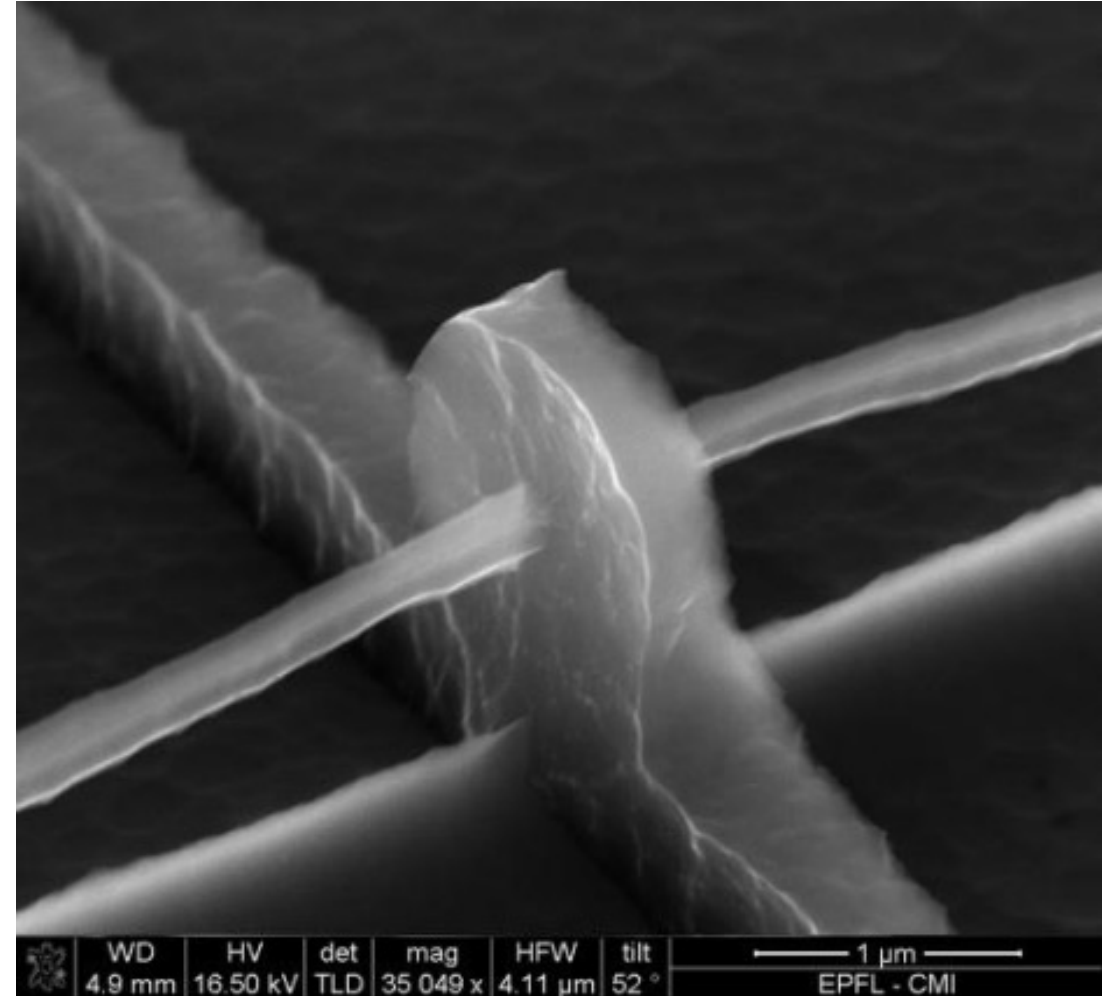


Fig. 3



Keep Moore's Law Alive

- We must find a way to keep increasing processing power
- Start building 3-dimensionally
 - Die-to-Die
 - Die-to-Wafer
 - Wafer-to-Wafer
- We want a singular, 3-dimensional semiconductor

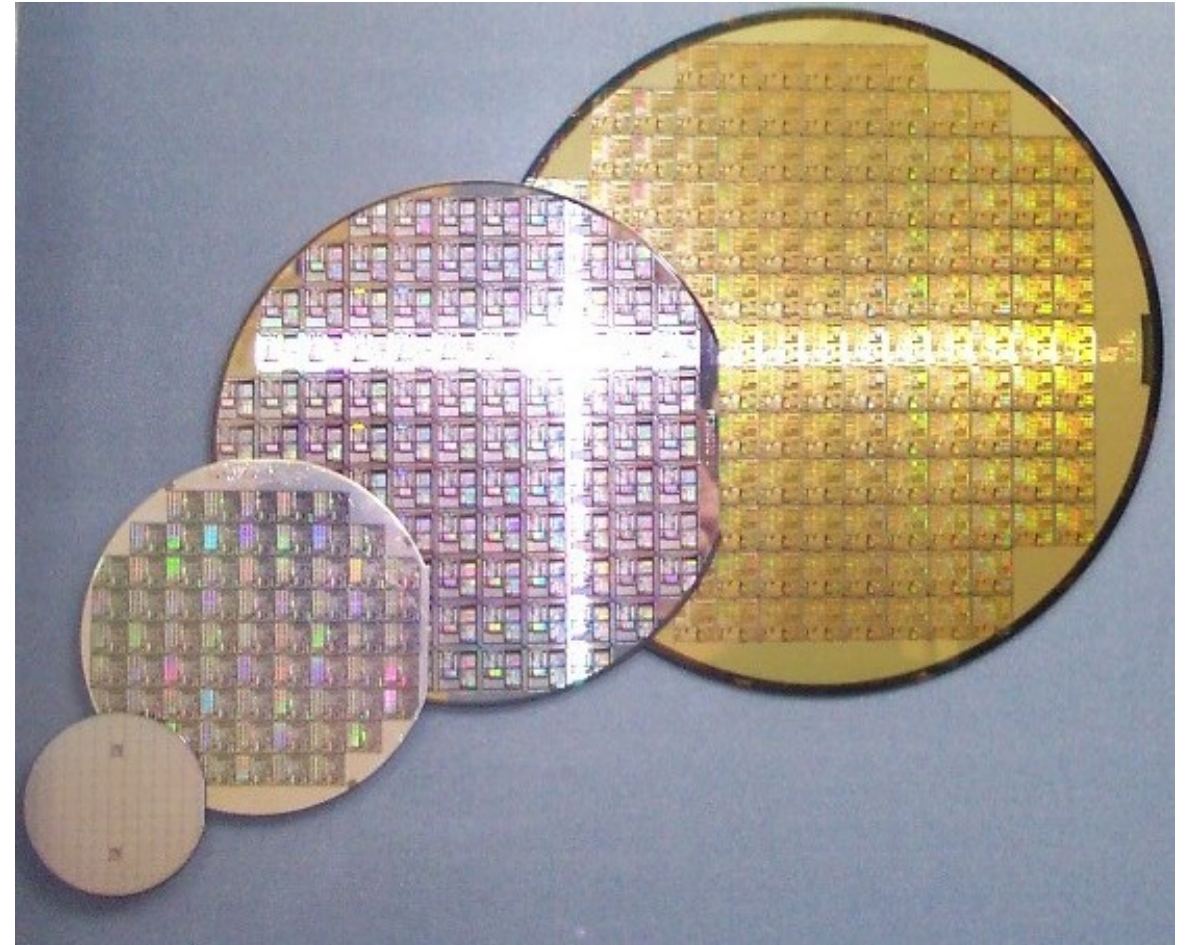
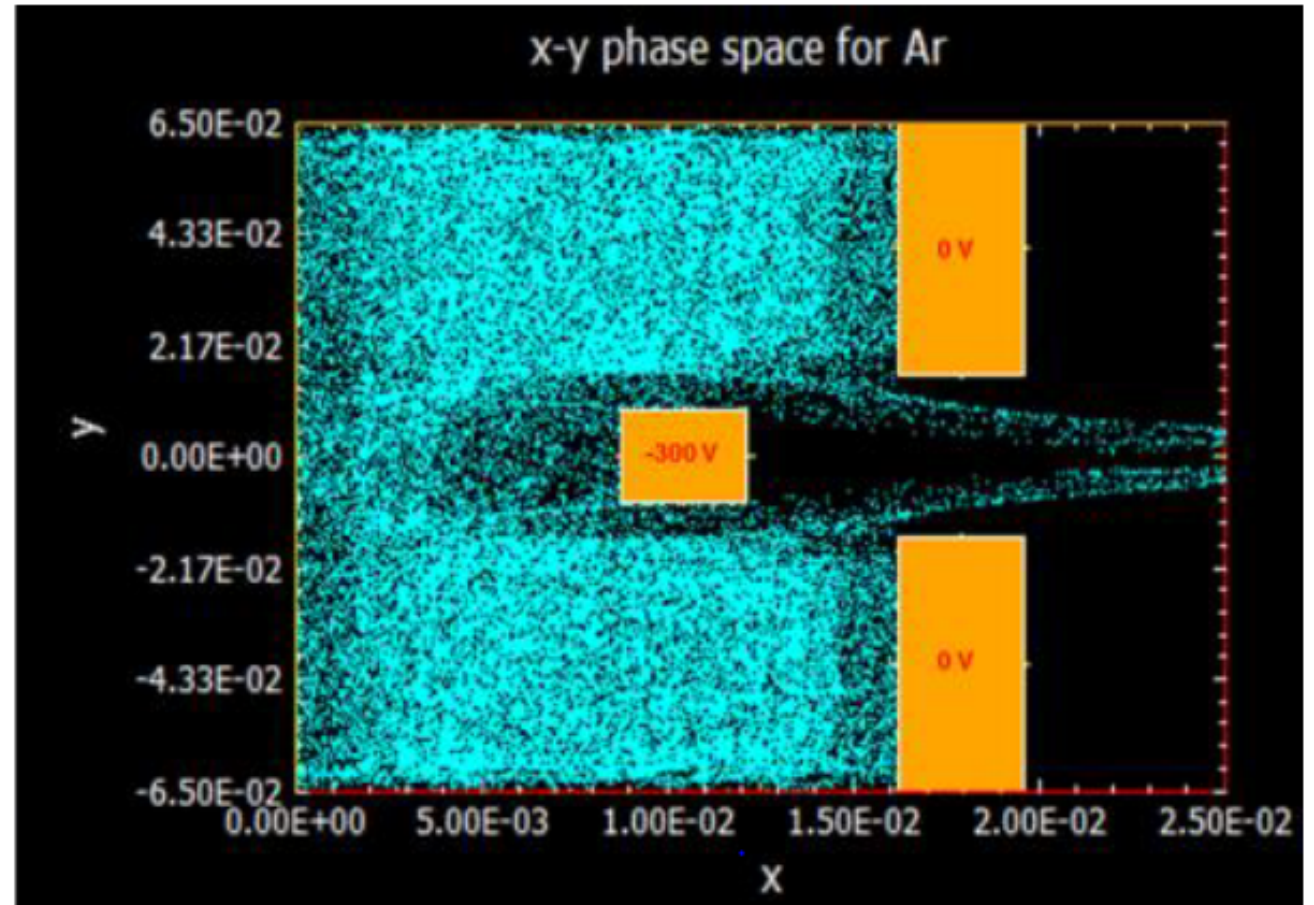


Fig. 4



Controllable Ion Beamlets

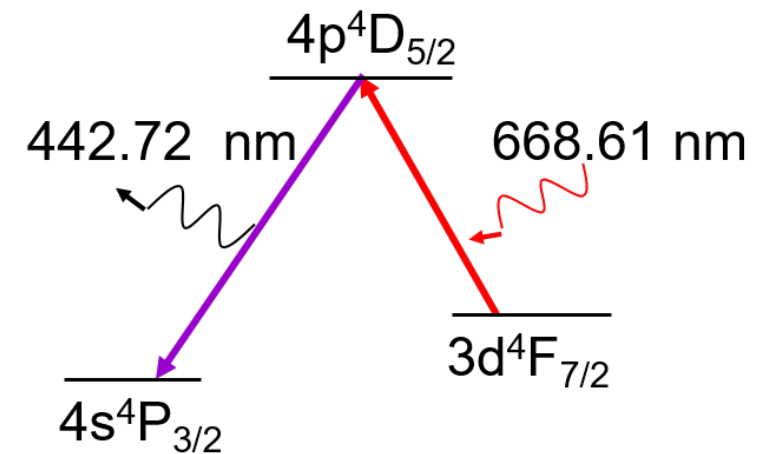
- NSF GOALIE Grant:
Optimization of Ion Beam Extraction – Enabling Technology For Advanced Semiconductor Fabrication
- Use LIF to investigate ion velocities and angular distribution dependences on source parameters.



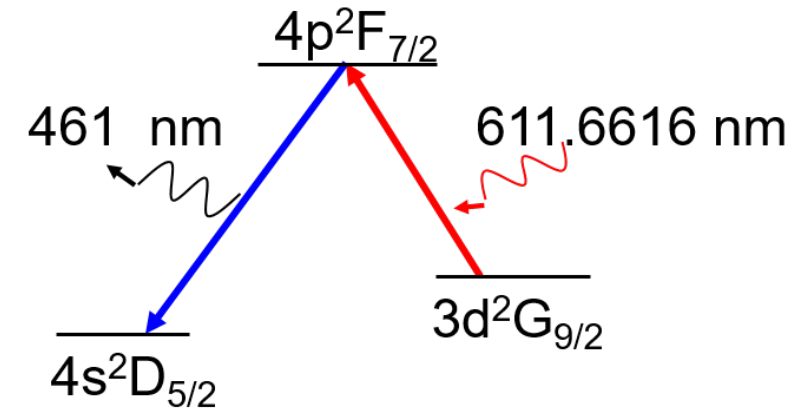
LIF

- Use laser to excite an electron to a higher state
- Collect emitted light when electron falls to more stable orbit
- Depending on velocity of ion it will “see” different wavelength of injected light
 - Can use this Doppler shift

Ar II
diode
laser

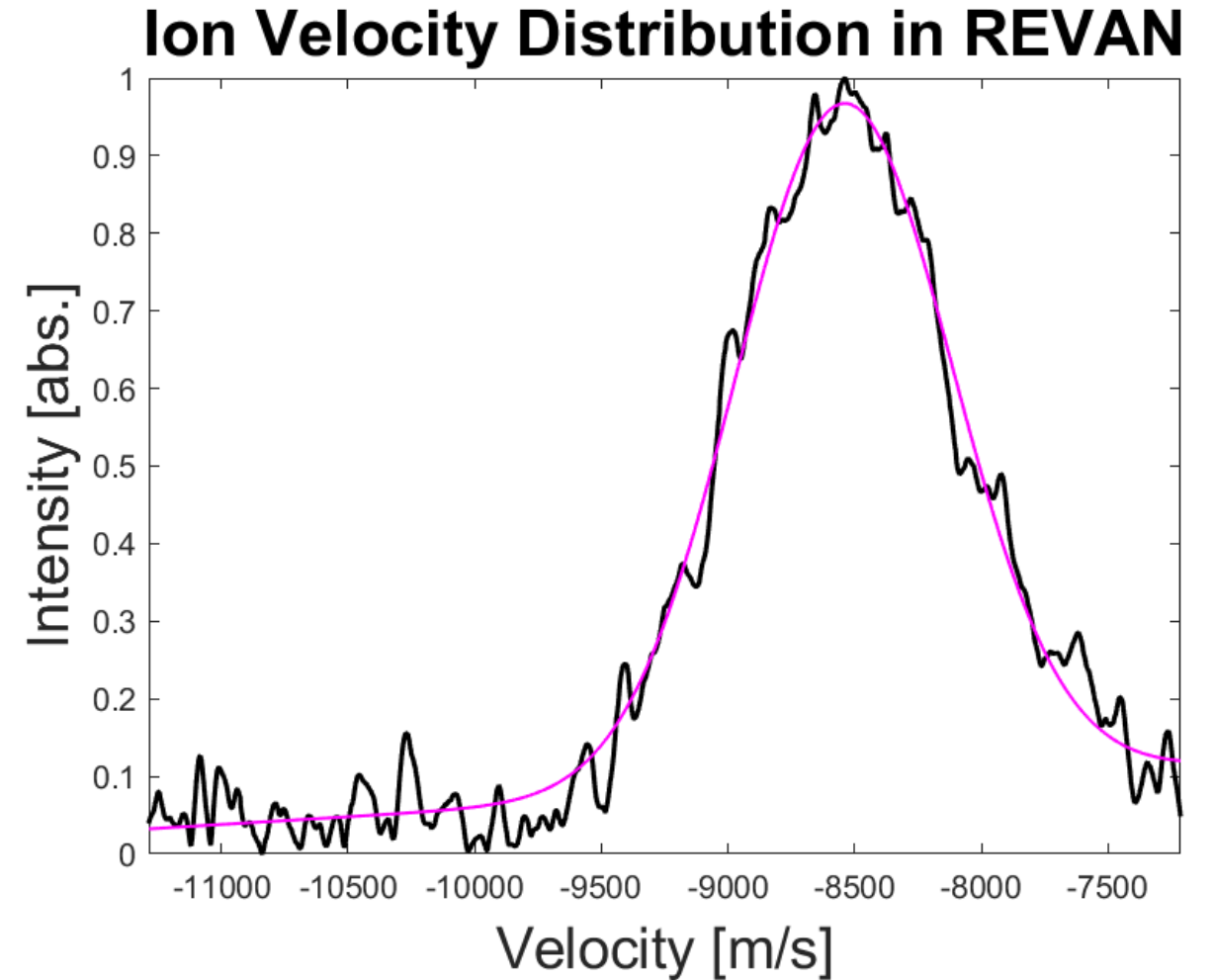


Ar II
dye
laser



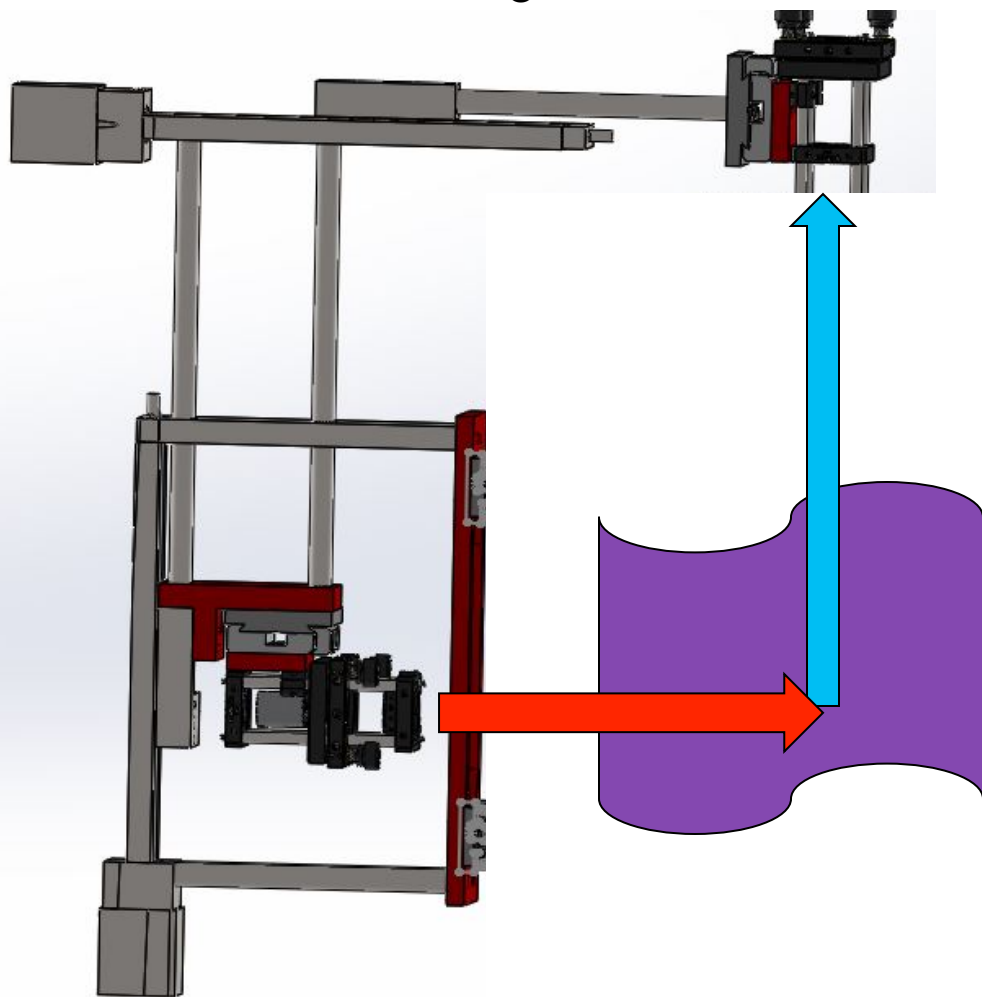
LIF

- Scan laser over frequency range
- Assume Maxwellian Distribution
- Fit Gaussian to IVDF
 - Area under curve \rightarrow Density
 - Offset \rightarrow Velocity
 - Width \rightarrow Temperature



LIF

2D Stage

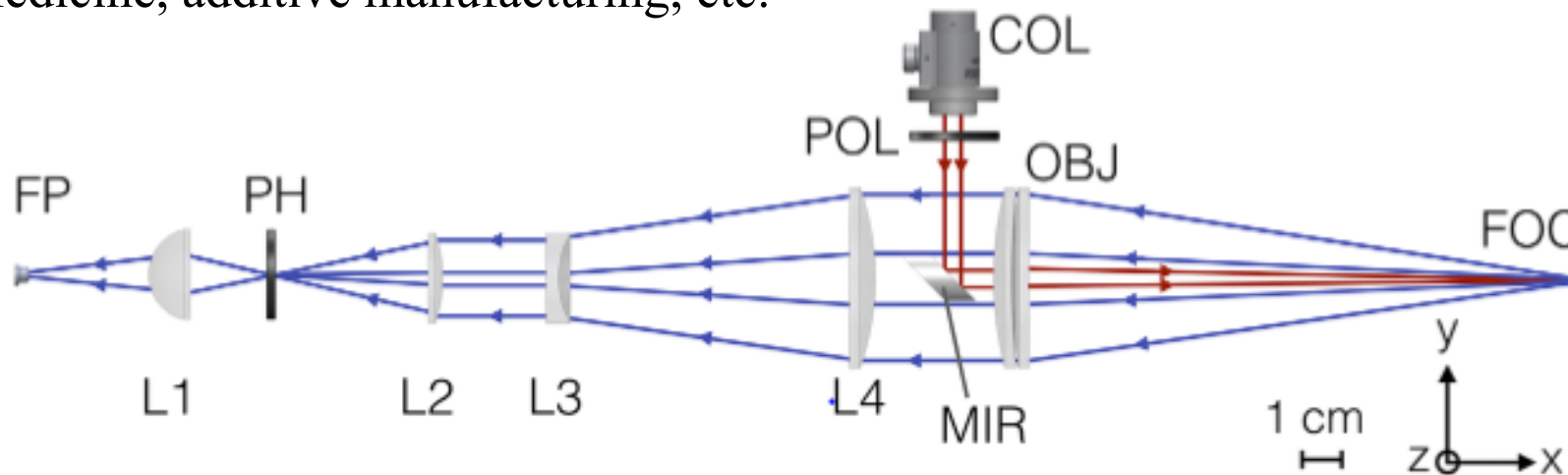


- Standard LIF needs two points of optical access
- Inject collimated beam to excite ions
- Collected with a focused optics to give localized measurement in plasma
- With enough optical access we can map the density, velocity, and temperature of the whole plasma

LIF

- Developed at WVU
- Allows for collection and injection along the same optical path
- Lets us measure previously forbidden regions of plasmas such as in antenna
- Many applications outside of plasma physics
 - Medicine, additive manufacturing, etc.

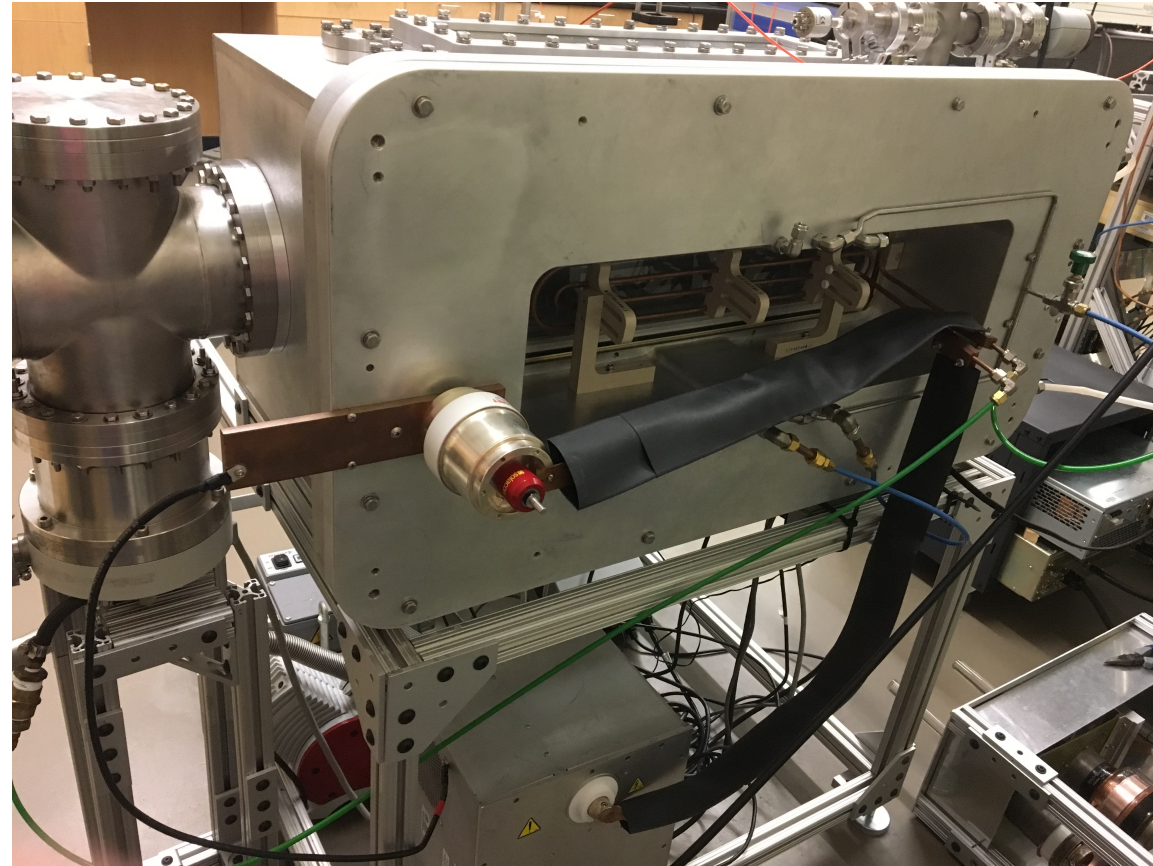
Confocal LIF



D.S. Thompson (2017)

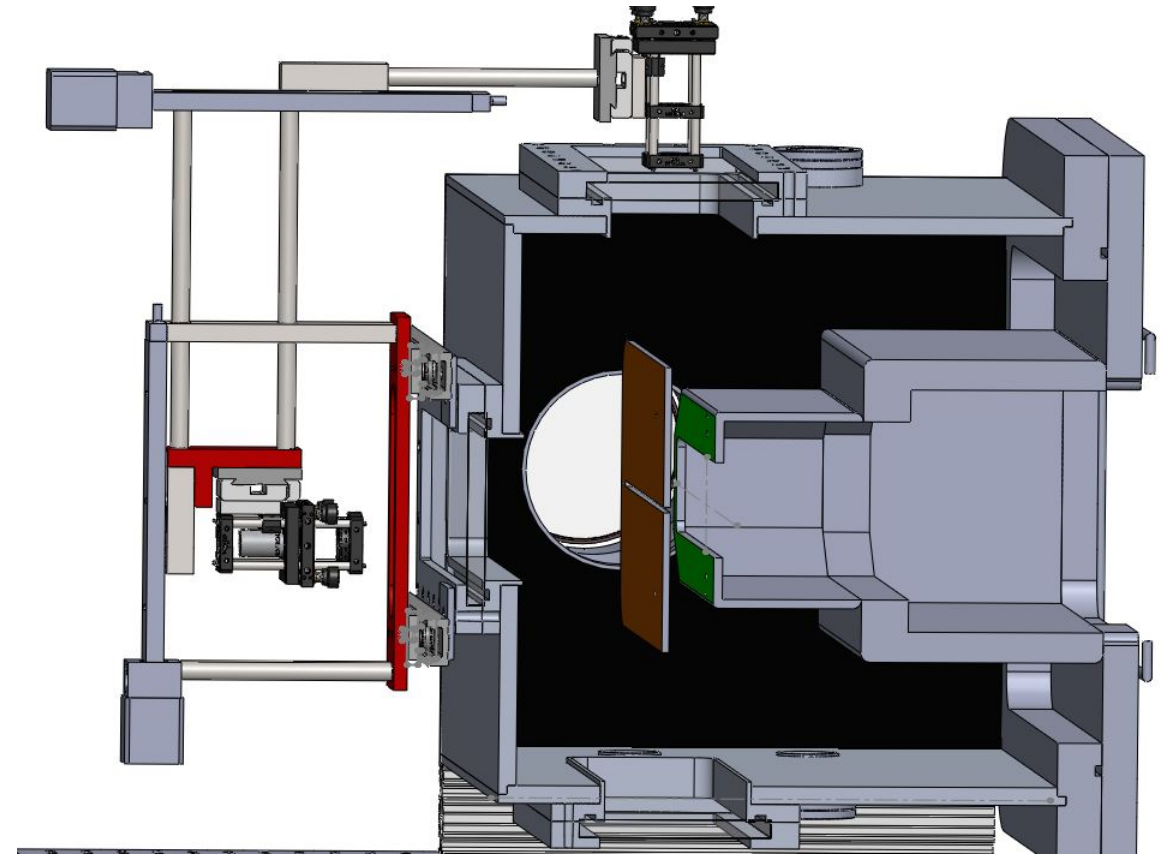


Ribbon Experiment for Velocity and Angular distribution (REVAN)

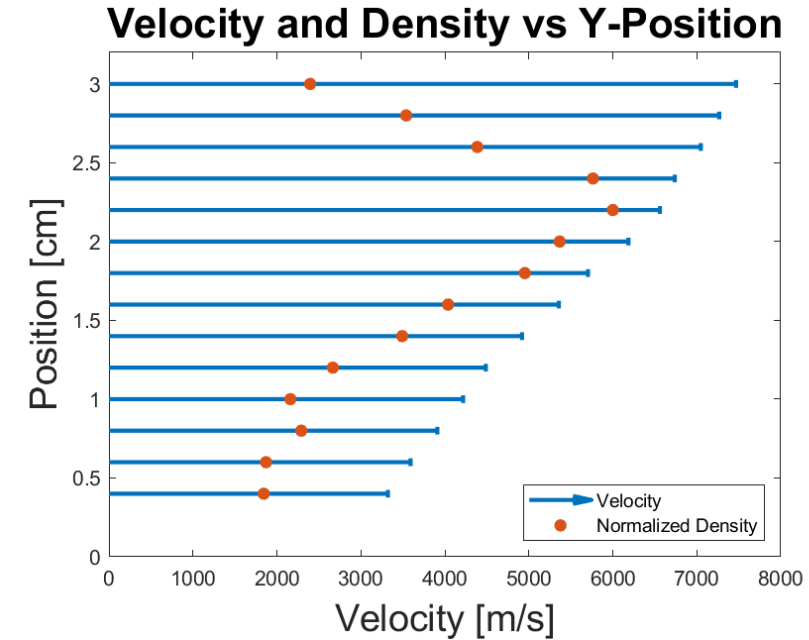
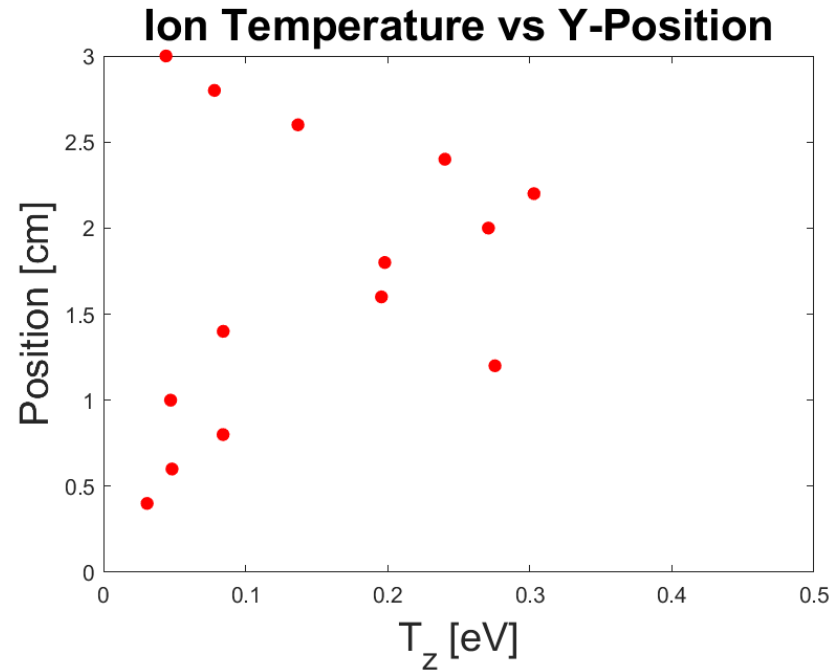
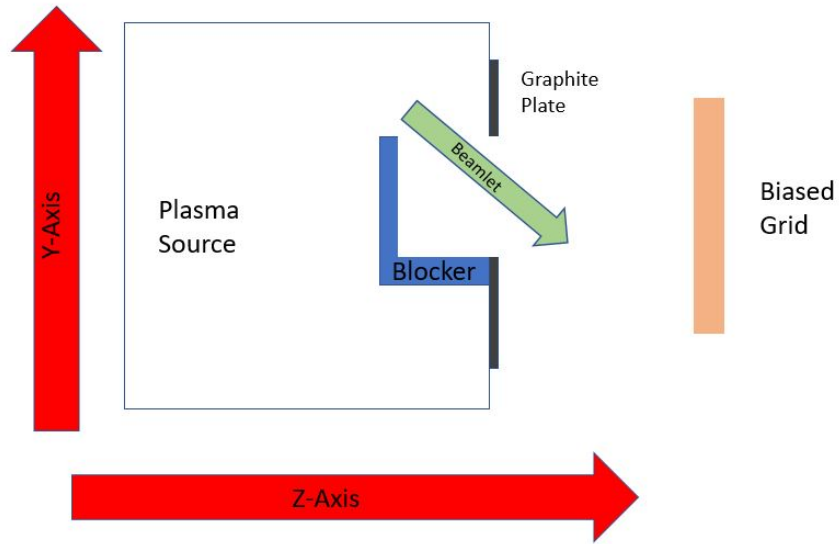


REVAN

- Orange plate mimics silicon wafer
 - Biased relative to plasma source
- Green marks exchangeable extraction optics
 - Different blocker geometry can create a double or single beamlet
- Source parameters:
 - Pressure
 - Power
 - Extraction Voltage



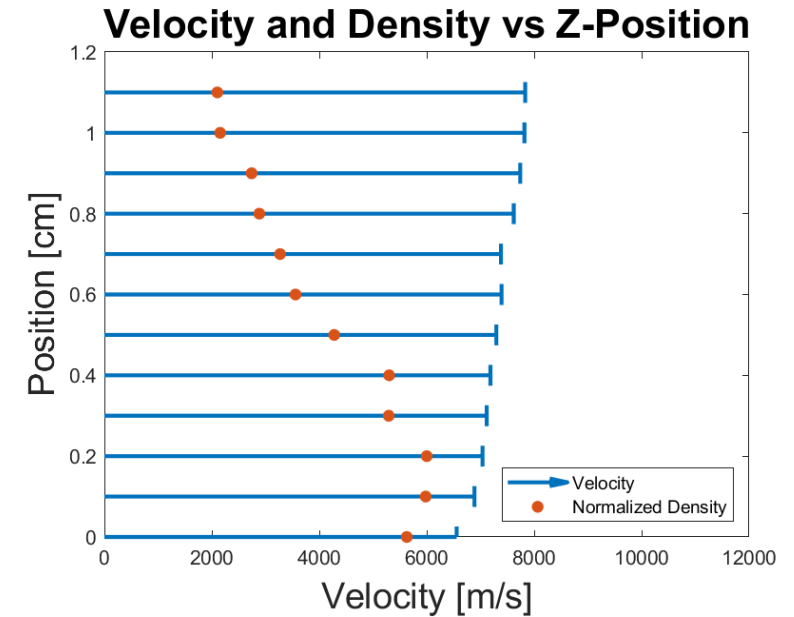
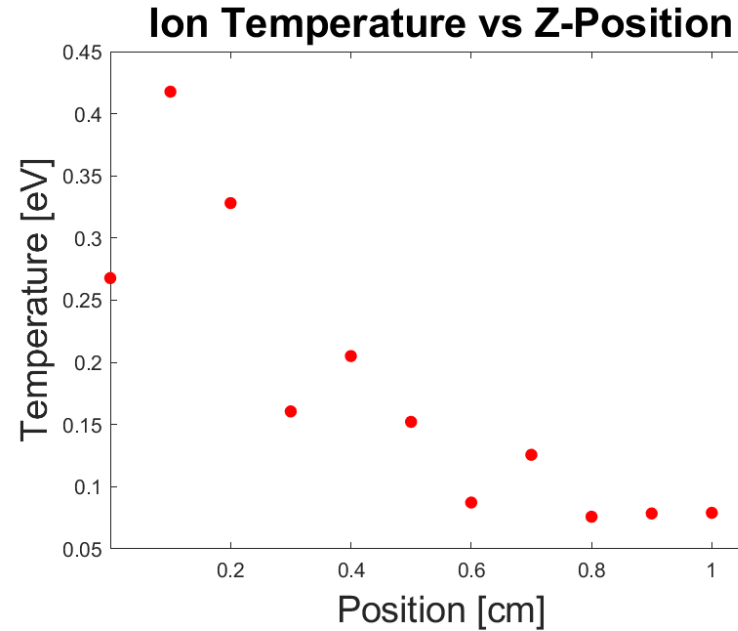
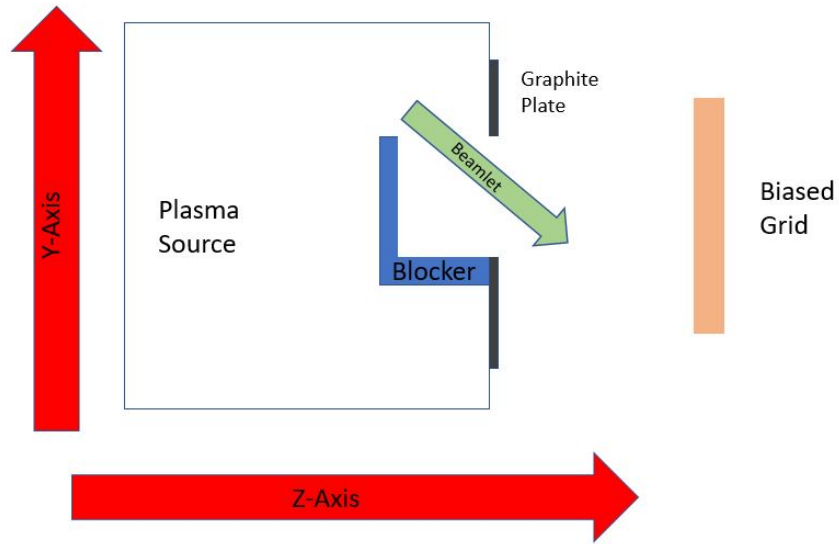
Results



- Held source parameters constant
- Looked “up and down” for beamlet



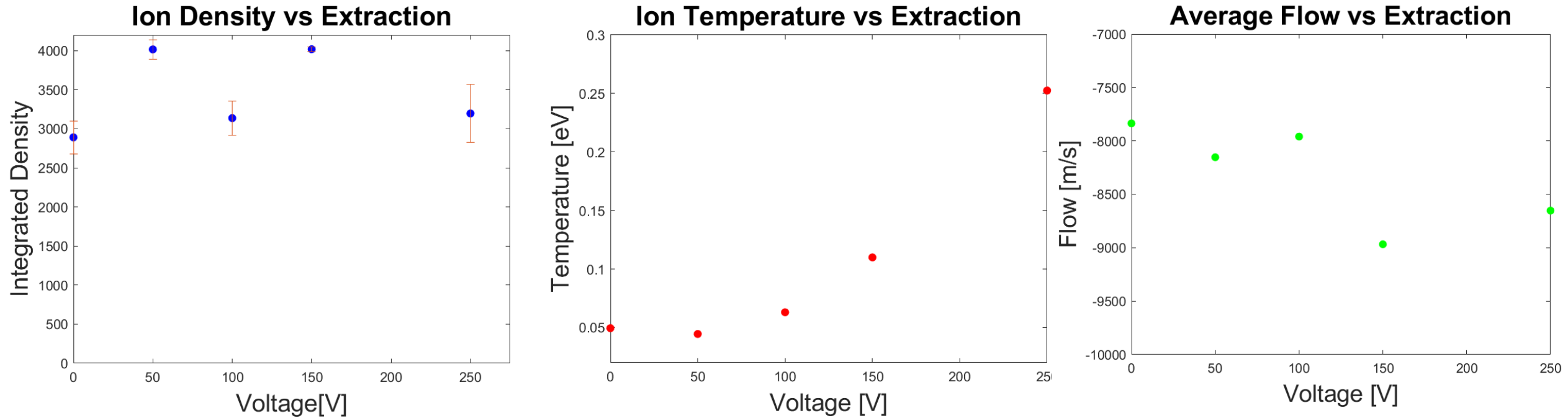
Results



- Held source parameters constant
- Looked “left and right” for beamlet



Extraction



- Pressure, Power and Position are held constant
- Varied the bias on the “wafer”

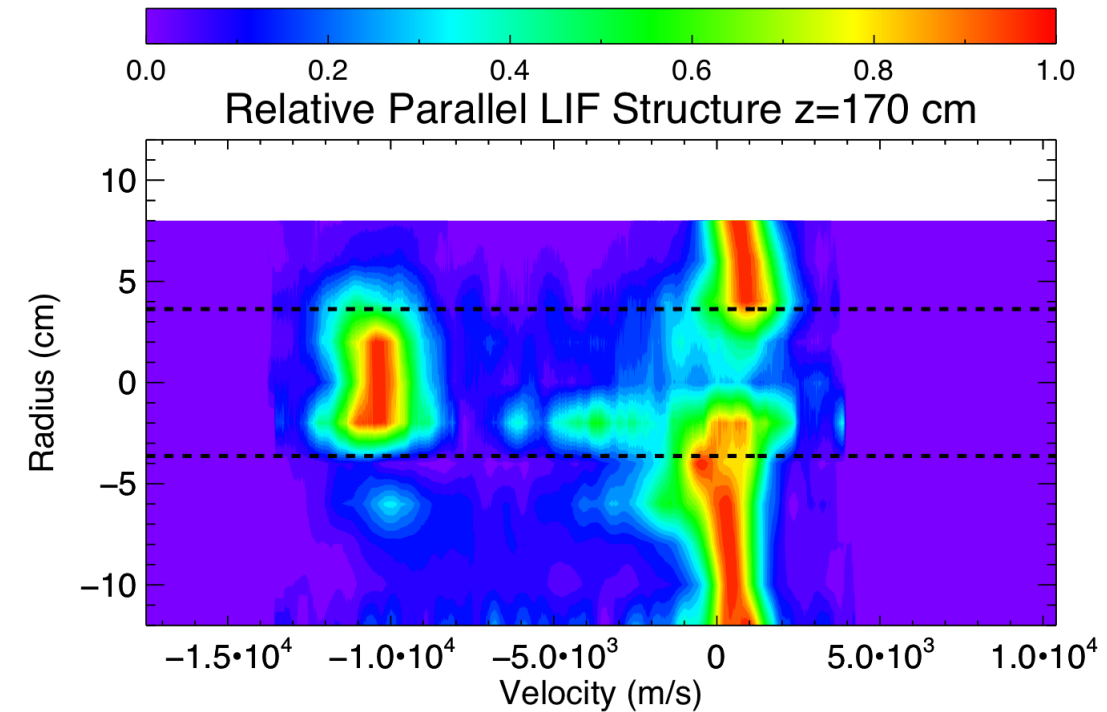
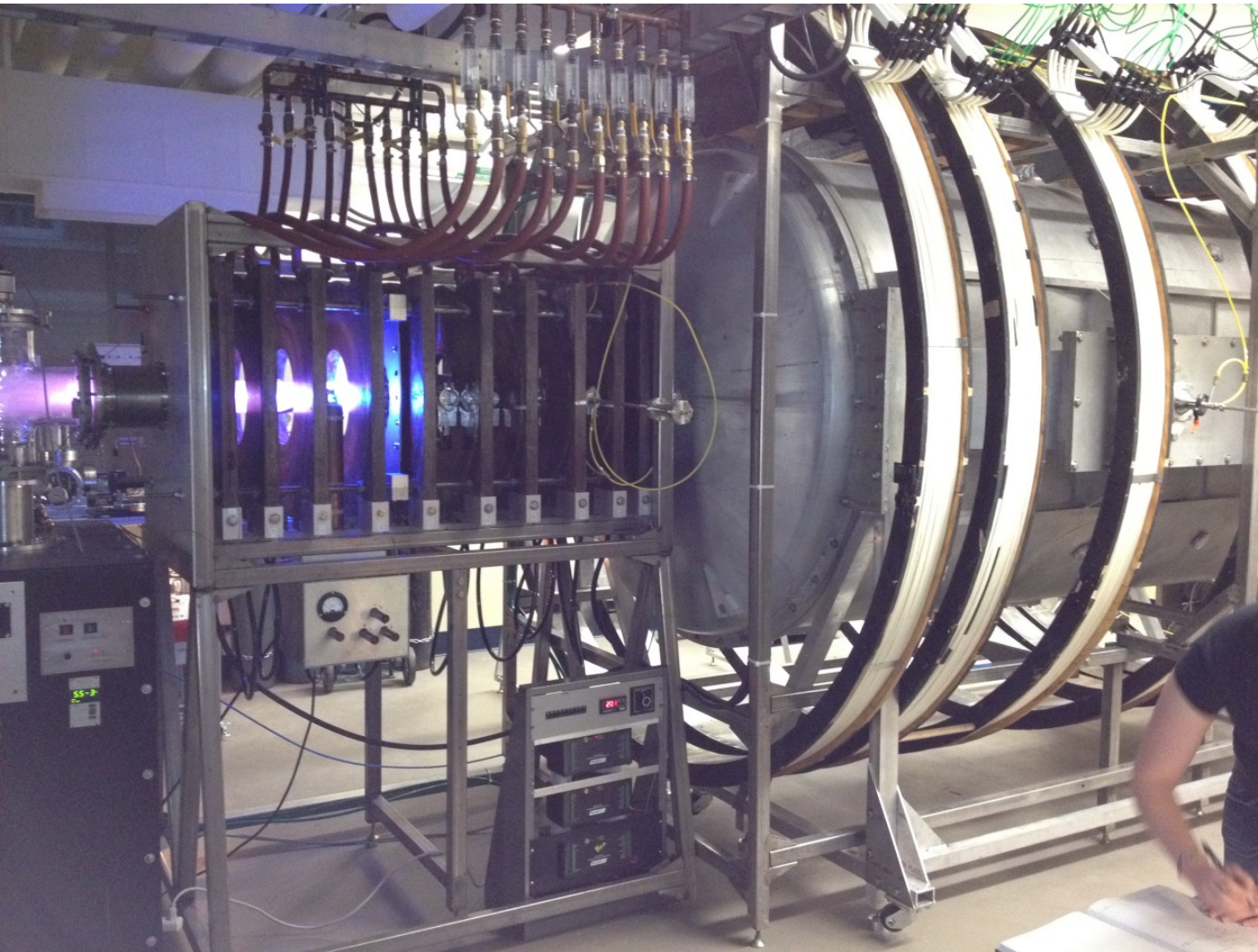


Results and Looking Forward

- We have confirmed the existence of an ion beamlet in REVAN
- Failed to see velocity increase with extraction voltage
 - Most likely not in “wafer” sheath
- Improve ion signal
- Create an ion density map of the beamlet
- Investigate new biased “wafer” structure

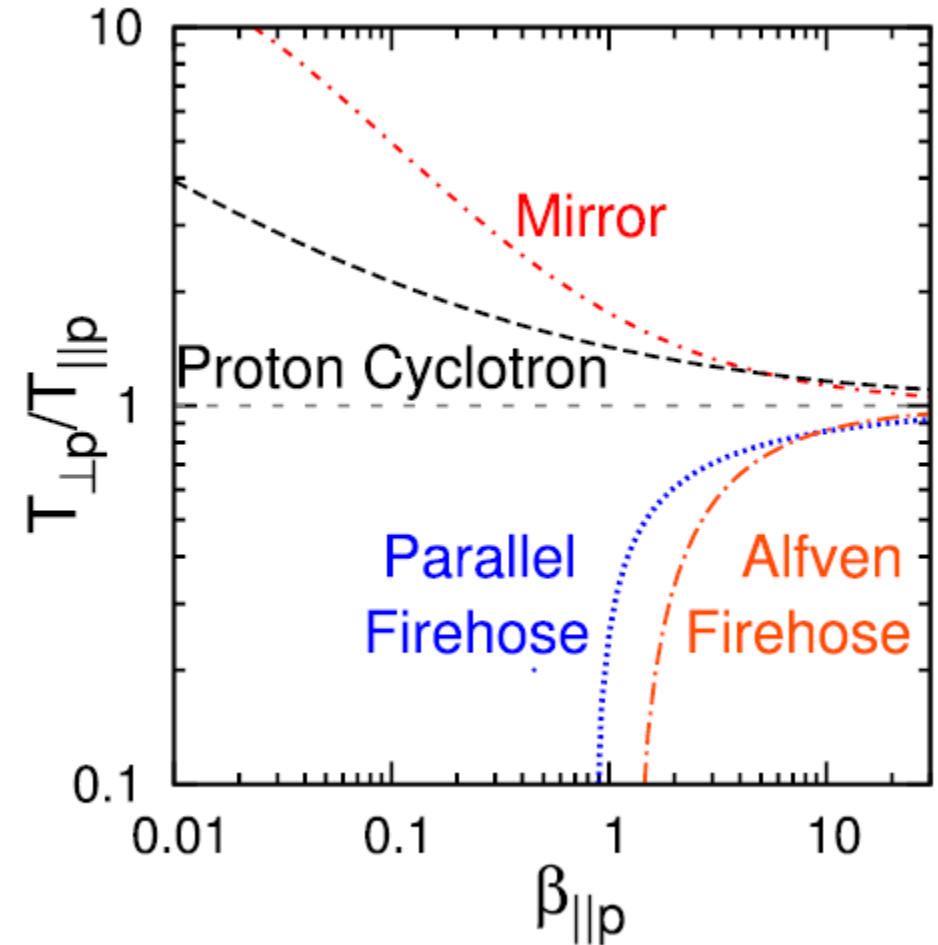


CURRENT PROJECTS – DOUBLE LAYERS



CURRENT PROJECTS – SOLAR ANISOTROPIC INSTABILITIES

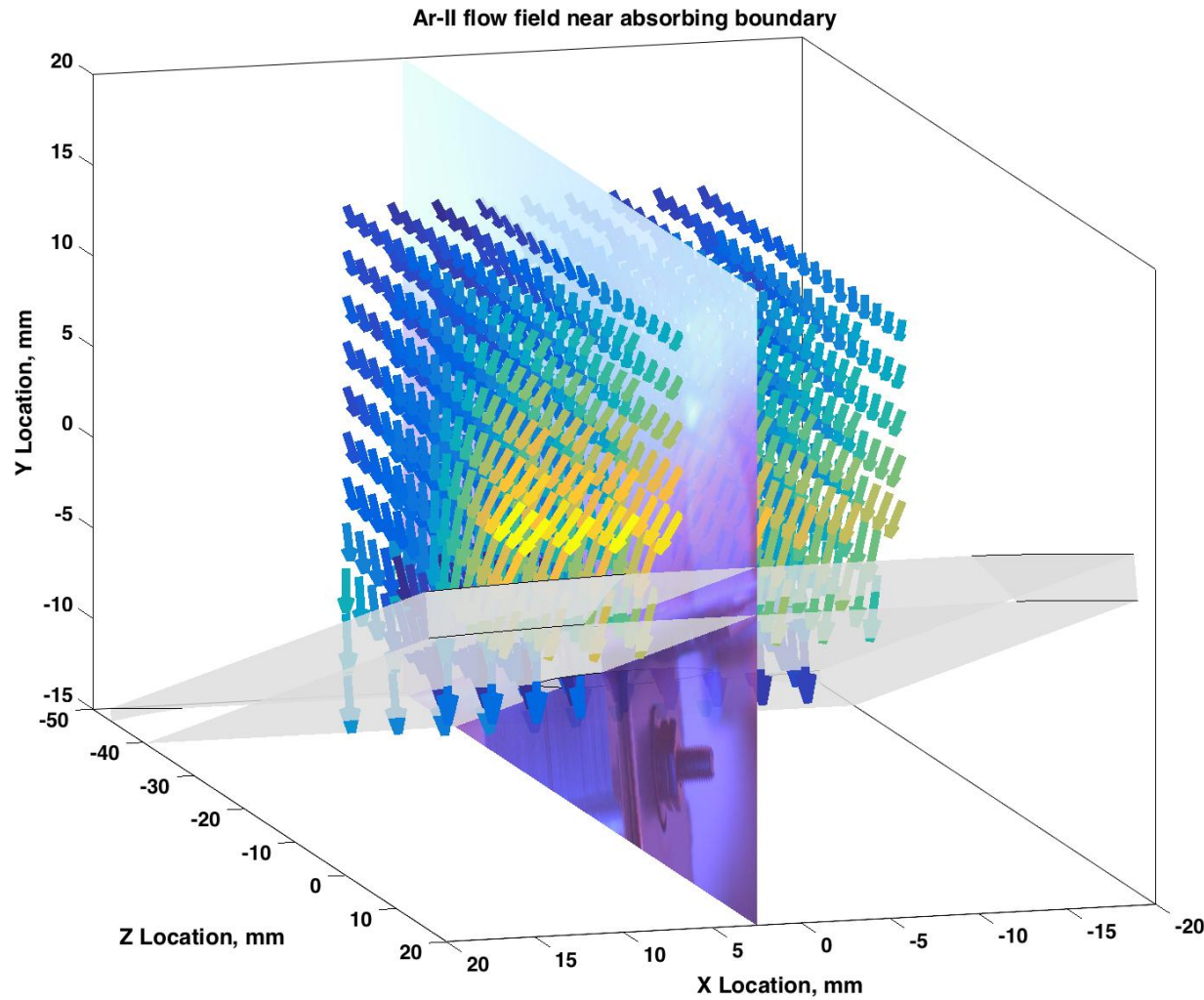
- Look at ion temperature in solar winds
- Whenever particles enter the instability regions their energy gets redirected or they are ejected in a loss cone
- Investigate if this holds for low beta plasmas with LIF and B-Dot probe



K.G. Klein (2015)



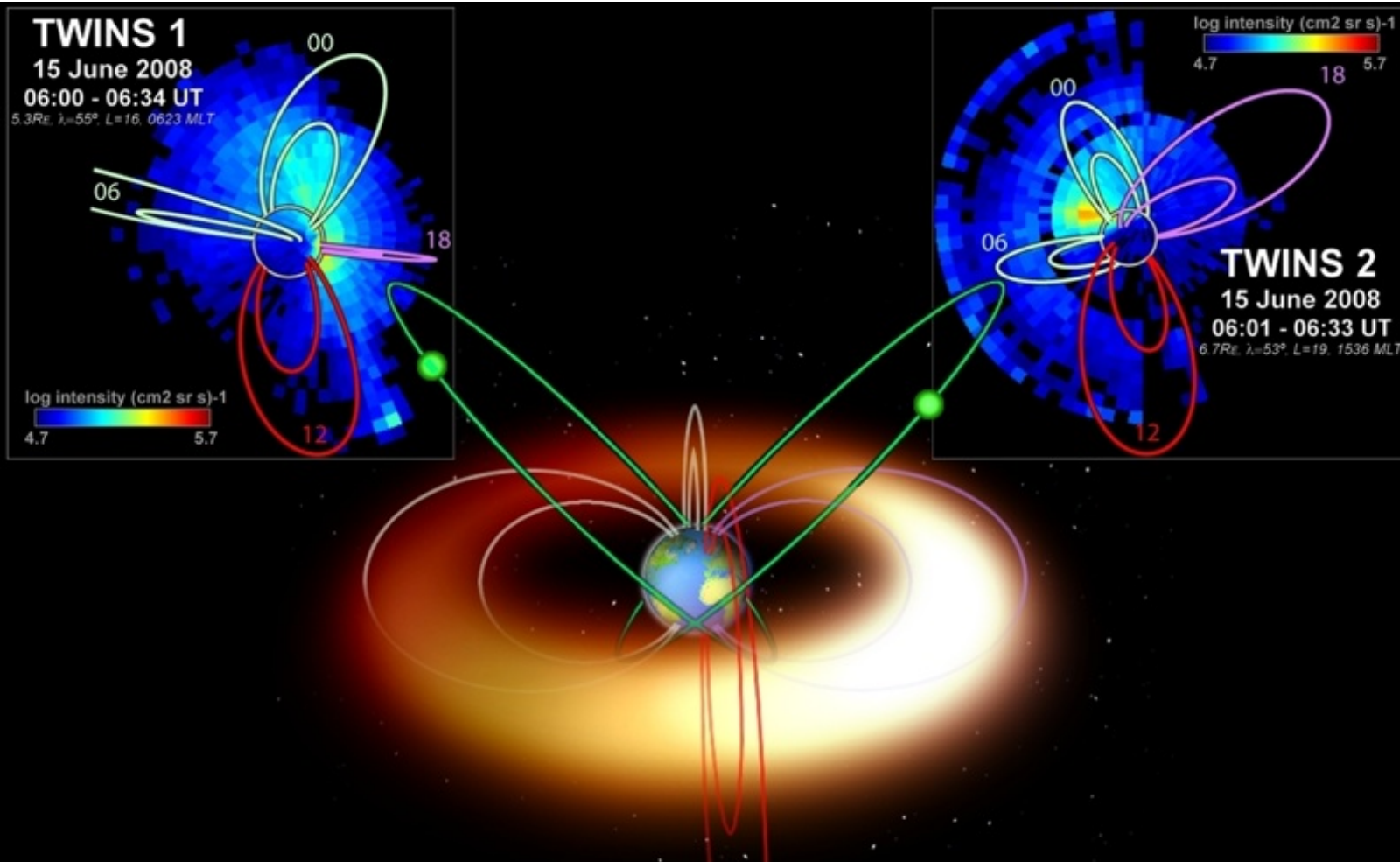
CURRENT PROJECTS – MAGNETIZED SHEATHS



In collaboration with UIUC – measurements of the full 3D flow field in a 3D volume to investigate the physics of magnetized sheaths for fusion wall and Hall thruster fundamental science.



CURRENT PROJECTS – SPACE IMAGING

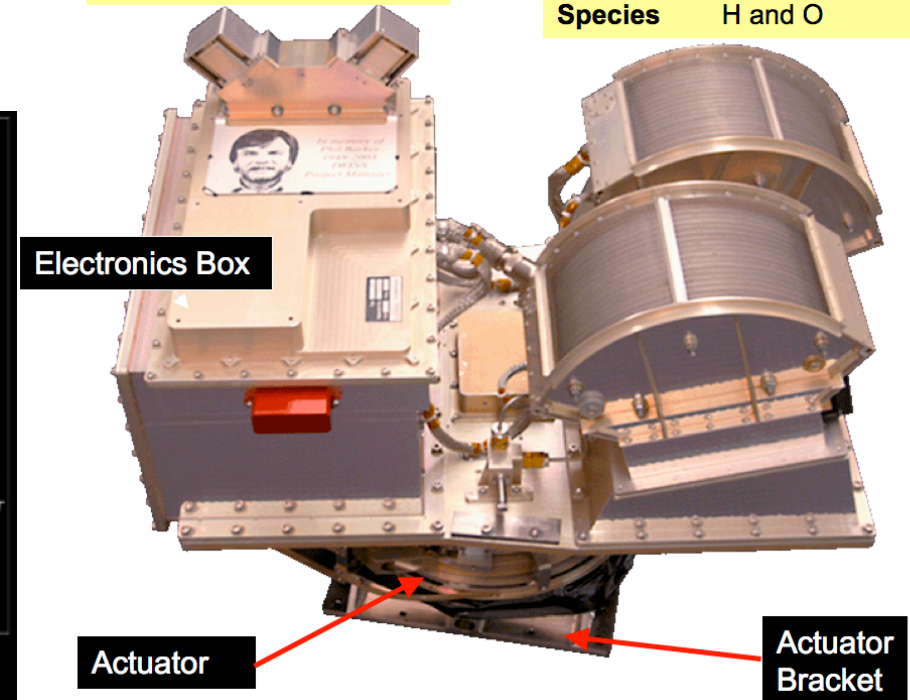


Ly-Alpha Detectors

Monitor geocorona
Photometer, Notch filter

ENA Sensor Heads

FOV	60° imaging / 2.5 sr
4° x 4°	(H > 10 keV)
1-100 keV	(H atoms)
Δt	60s (82s)
Species	H and O

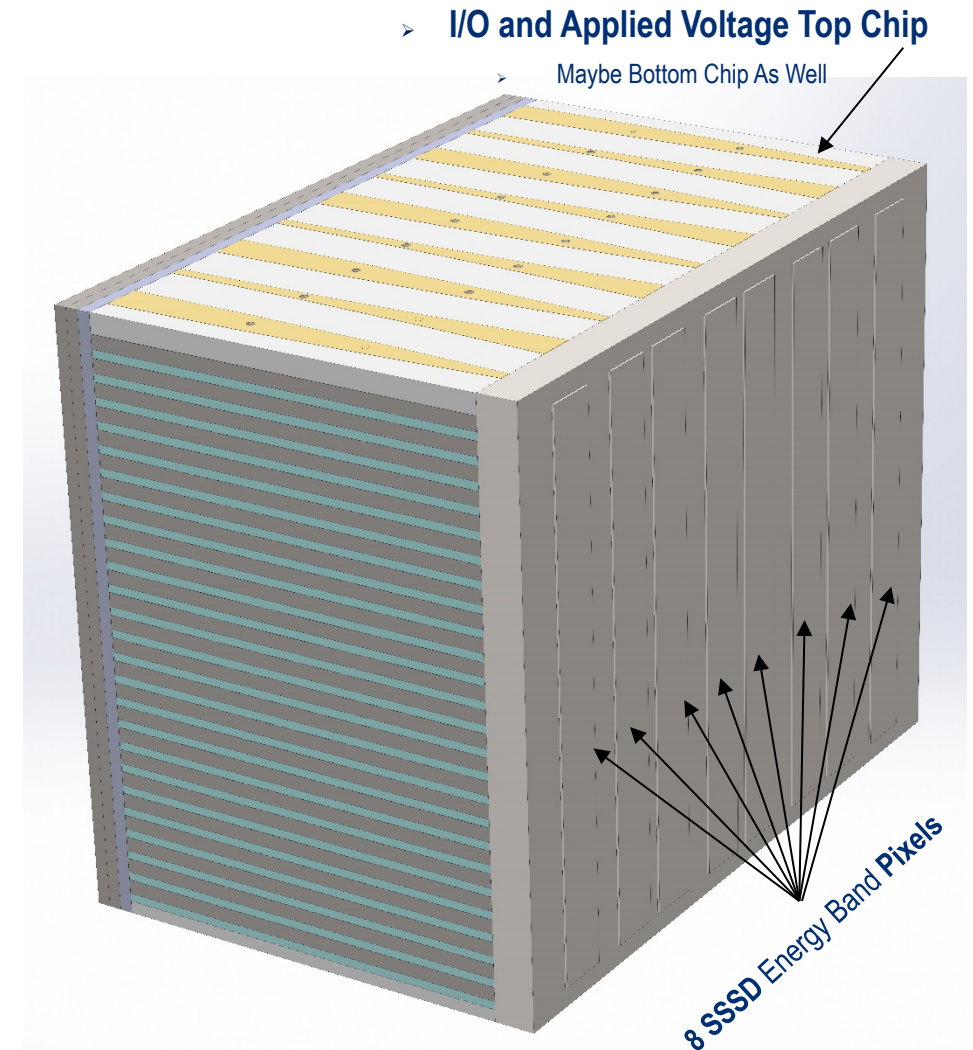
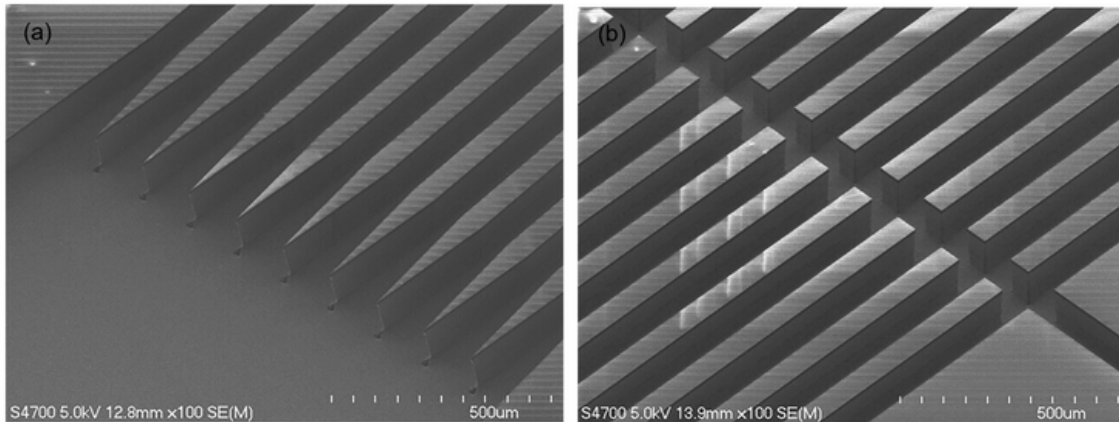


Look at the Earth's magnetosphere
by imaging charge exchange of
neutral atoms ($\sim 1\text{-}100$ keV)

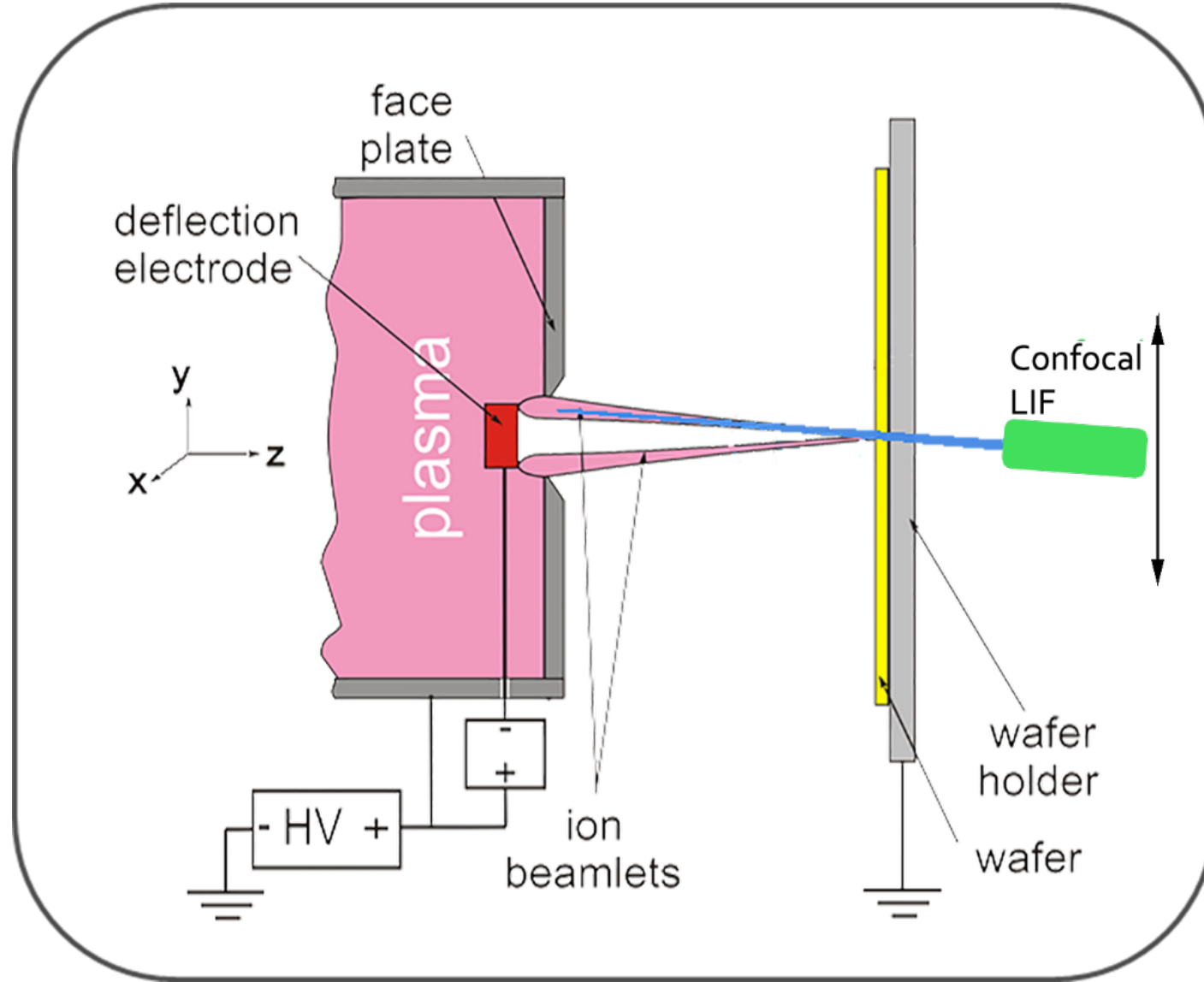


CURRENT PROJECTS- ULTRA COMPACT PLASMA SPECTROMETER

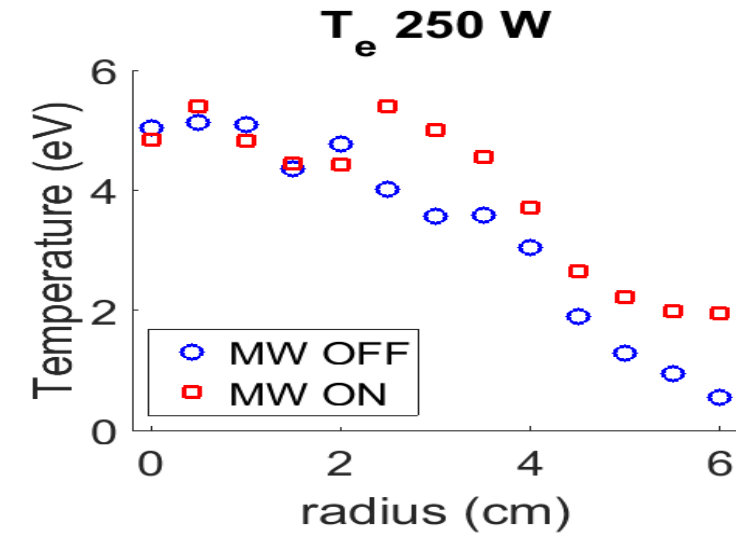
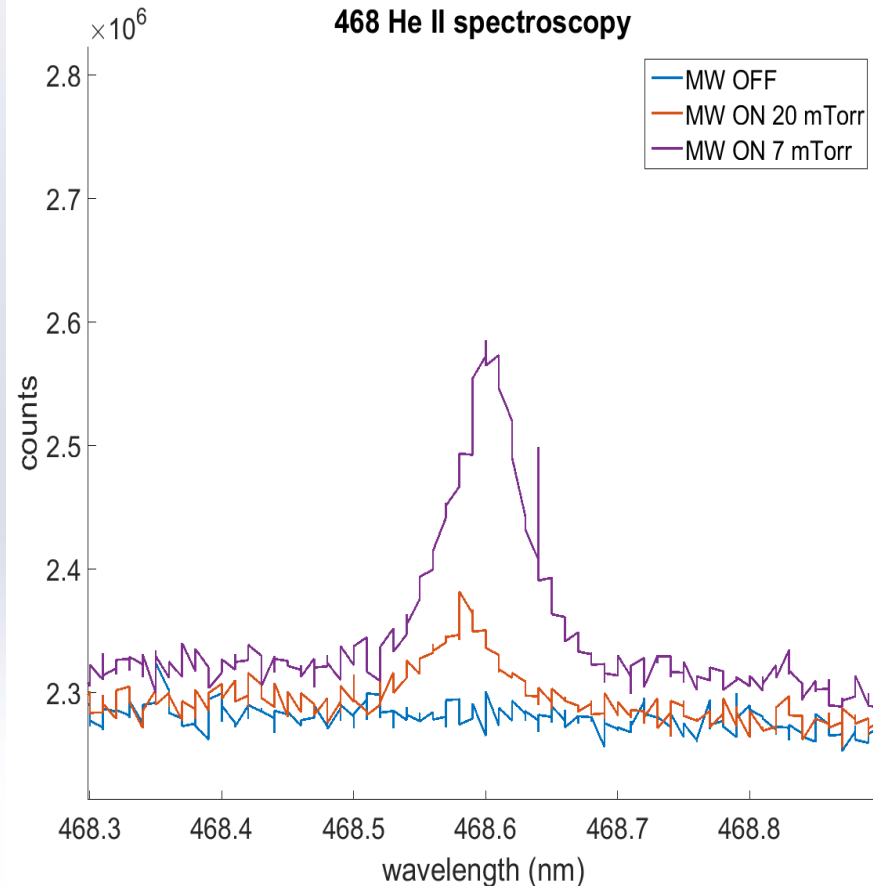
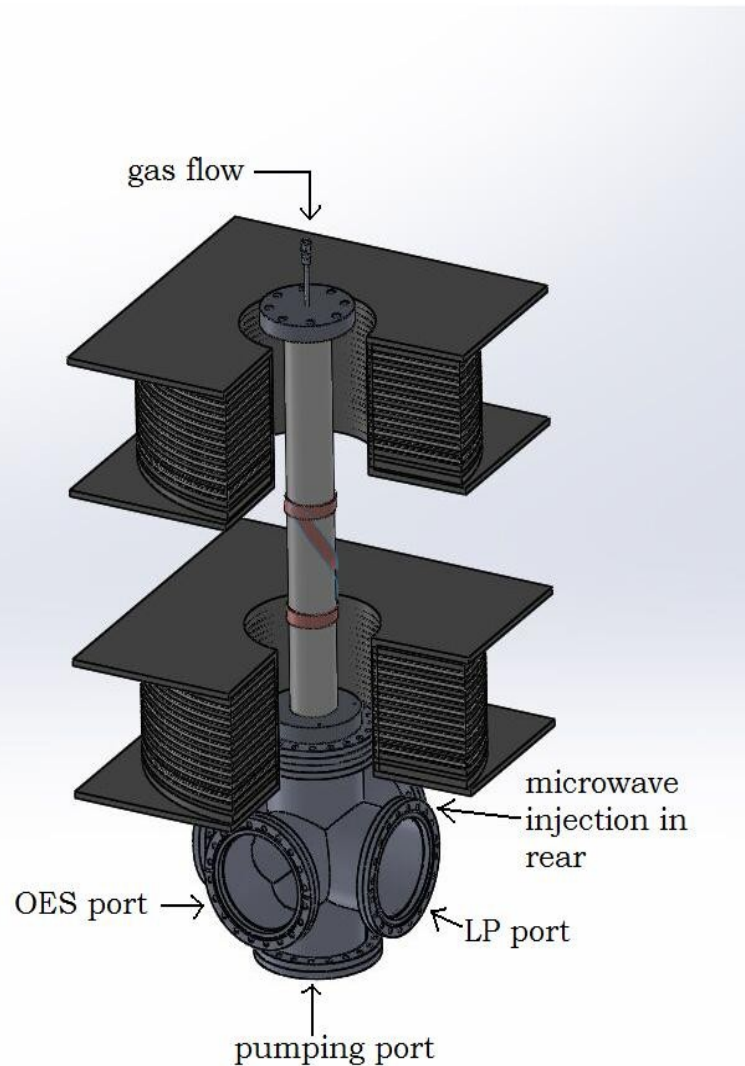
- In situ probes that can make direct, spatially resolved measurements of the ion energy spectra in the edge of tokamak.
- Must be easily replaced and requiring minimal resources.
- The ion spectrometers will consist of a combined collimator and energy analyzer fabricated from silicon
- Published results as of yesterday: A. M. Keesee, et al. (2018)



CURRENT PROJECTS – PLASMA ETCHING AND DEPOSITION



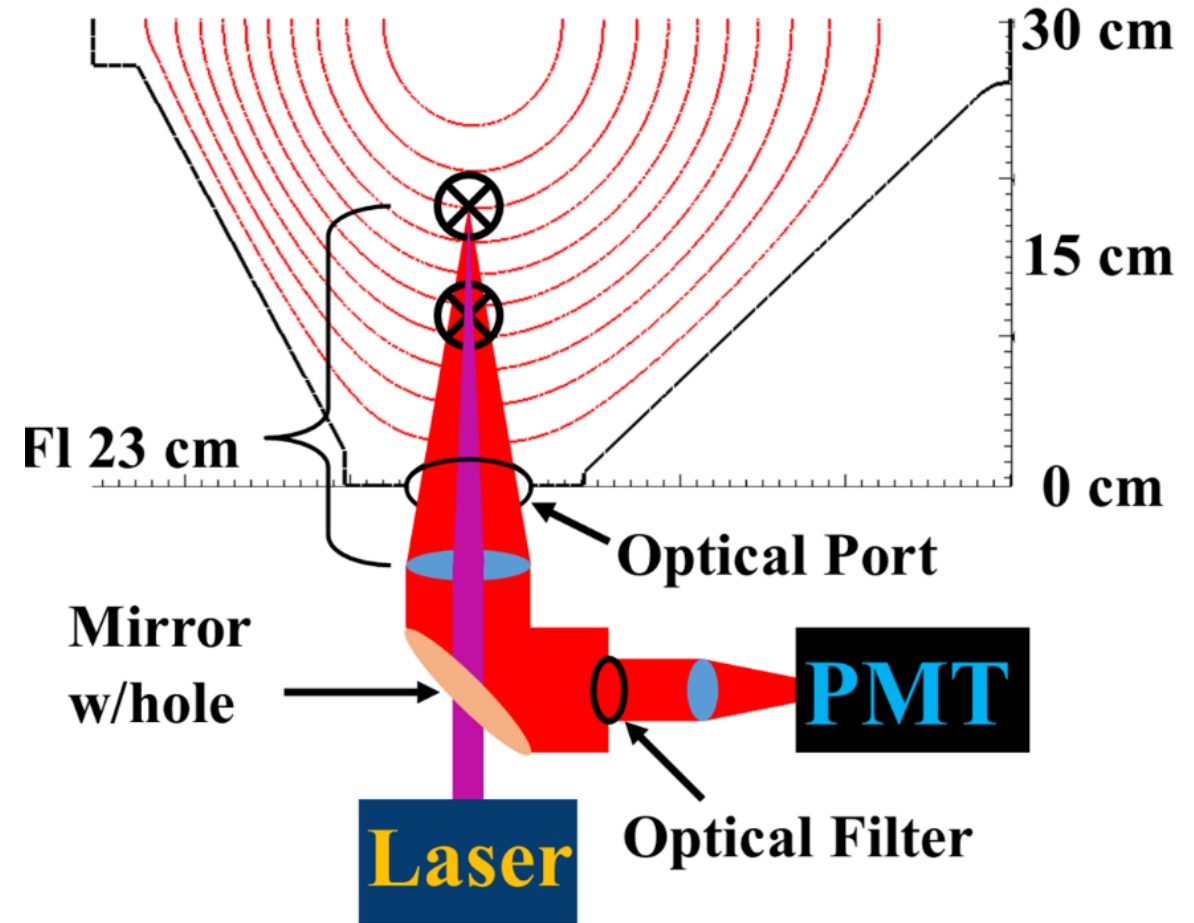
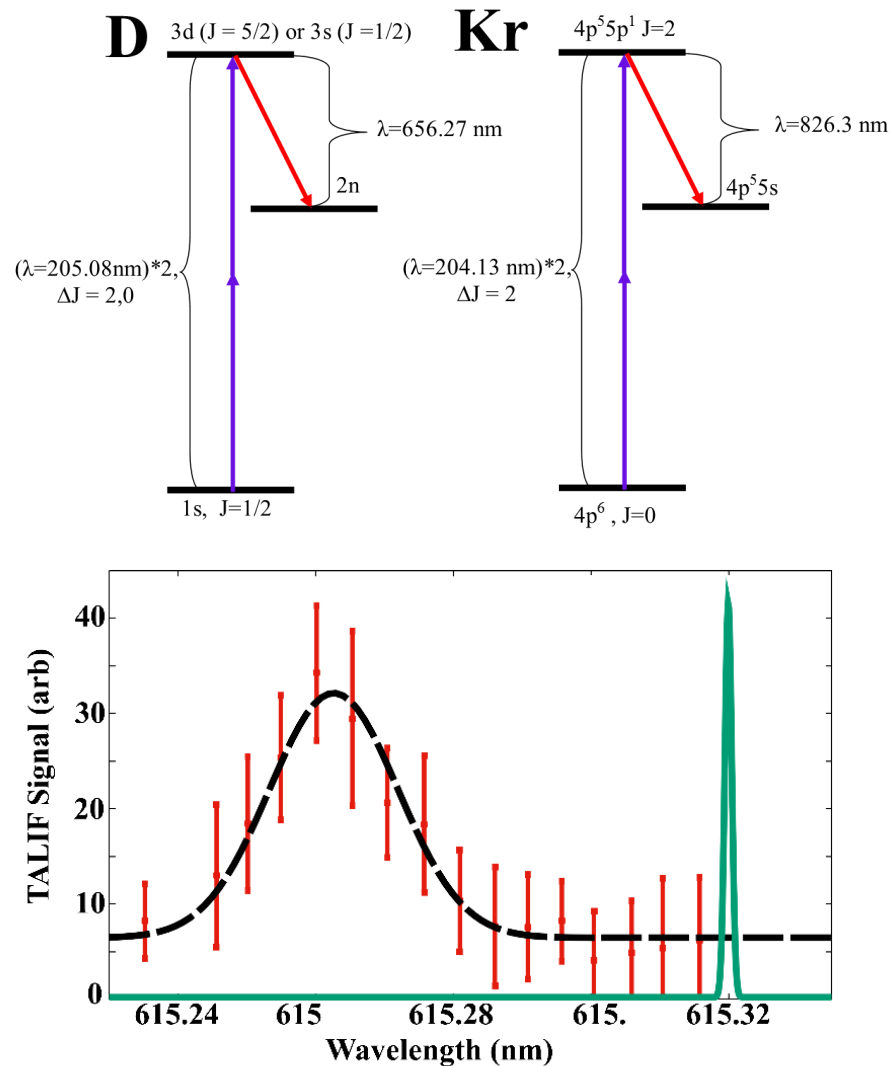
CURRENT PROJECTS – ELECTRON CYCLOTRON HEATING



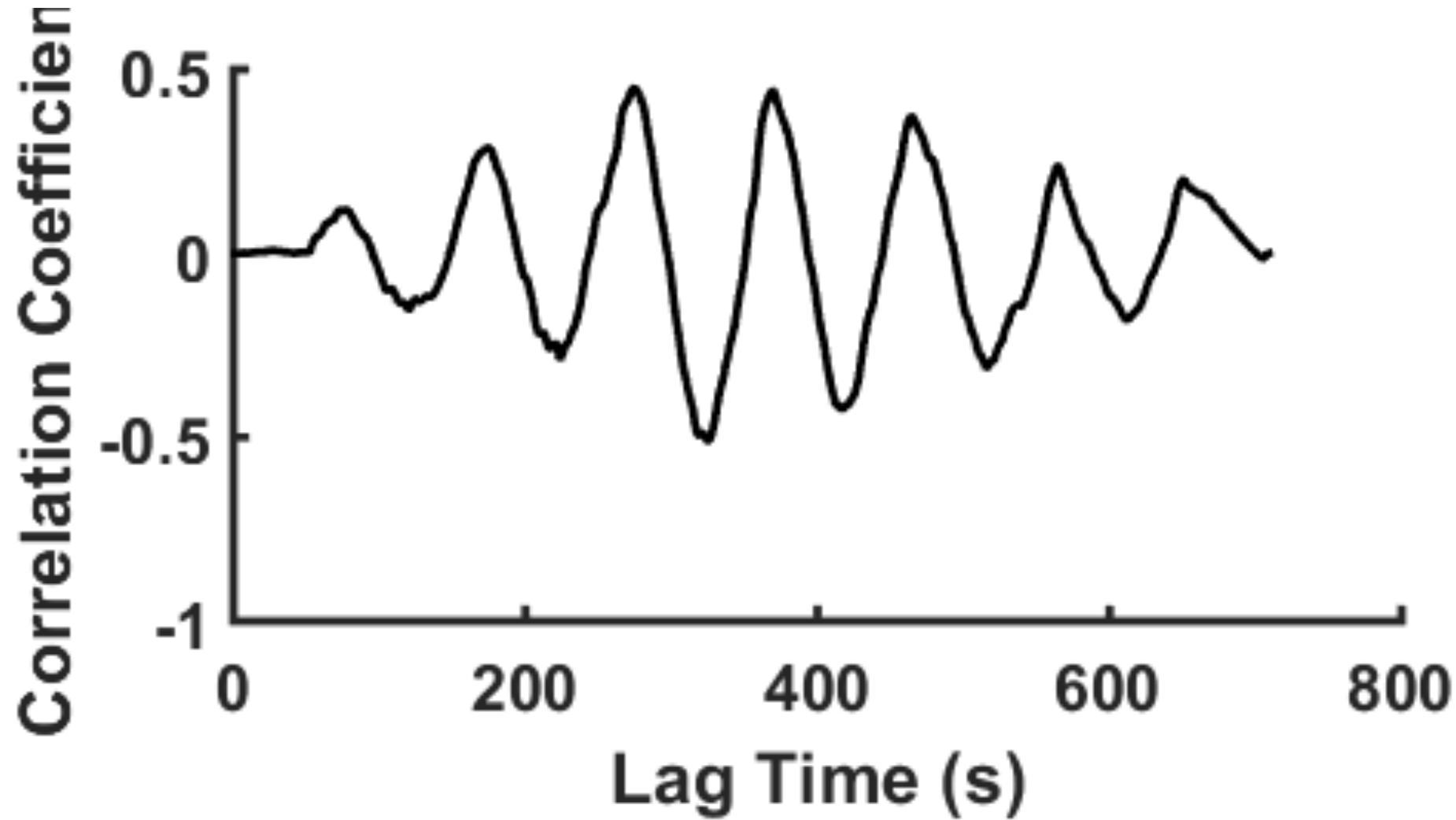
- Wanted to see if x-rays could excite electrons in He plasma to higher energy states
- Langmuir measurements and OES confirmed that the electron gained energy and were excited has high as $n = 6$



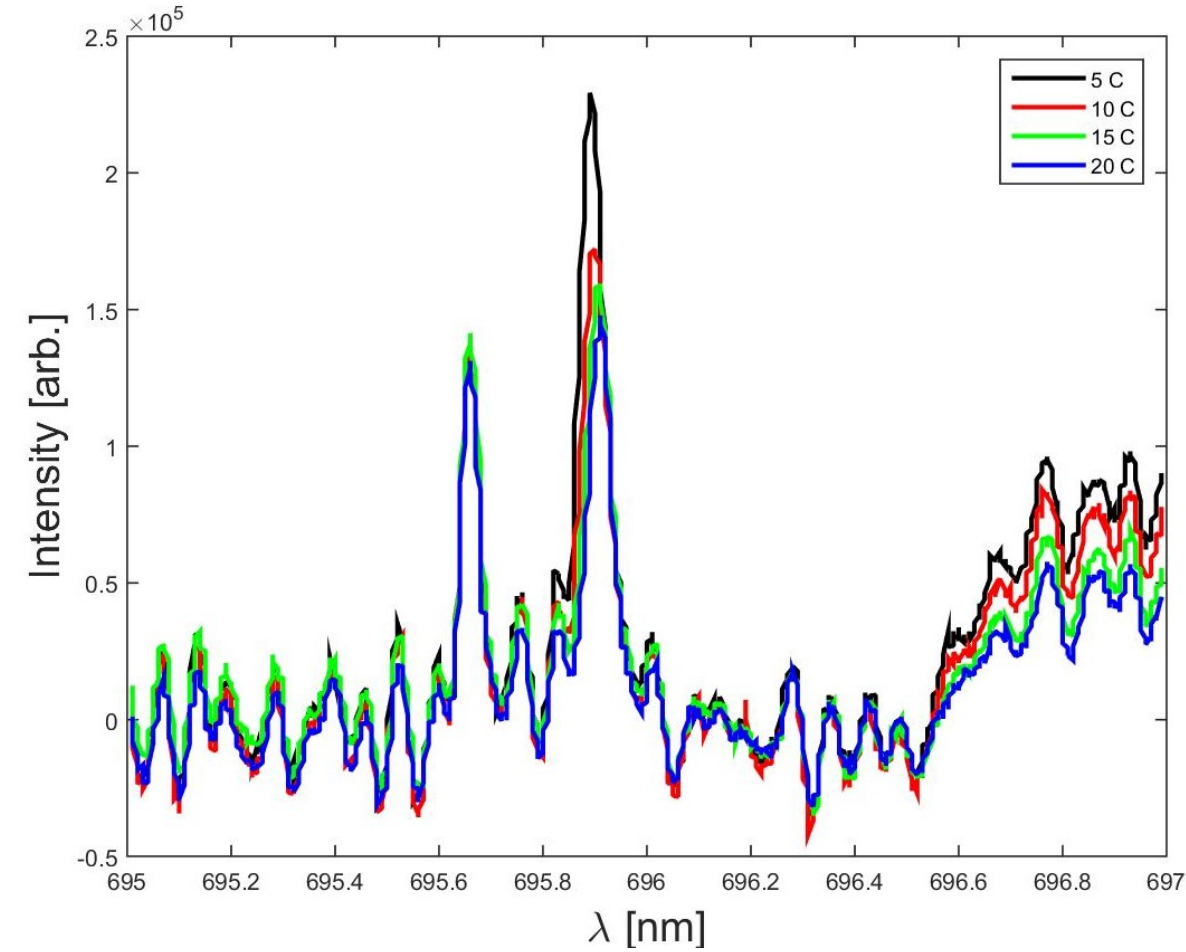
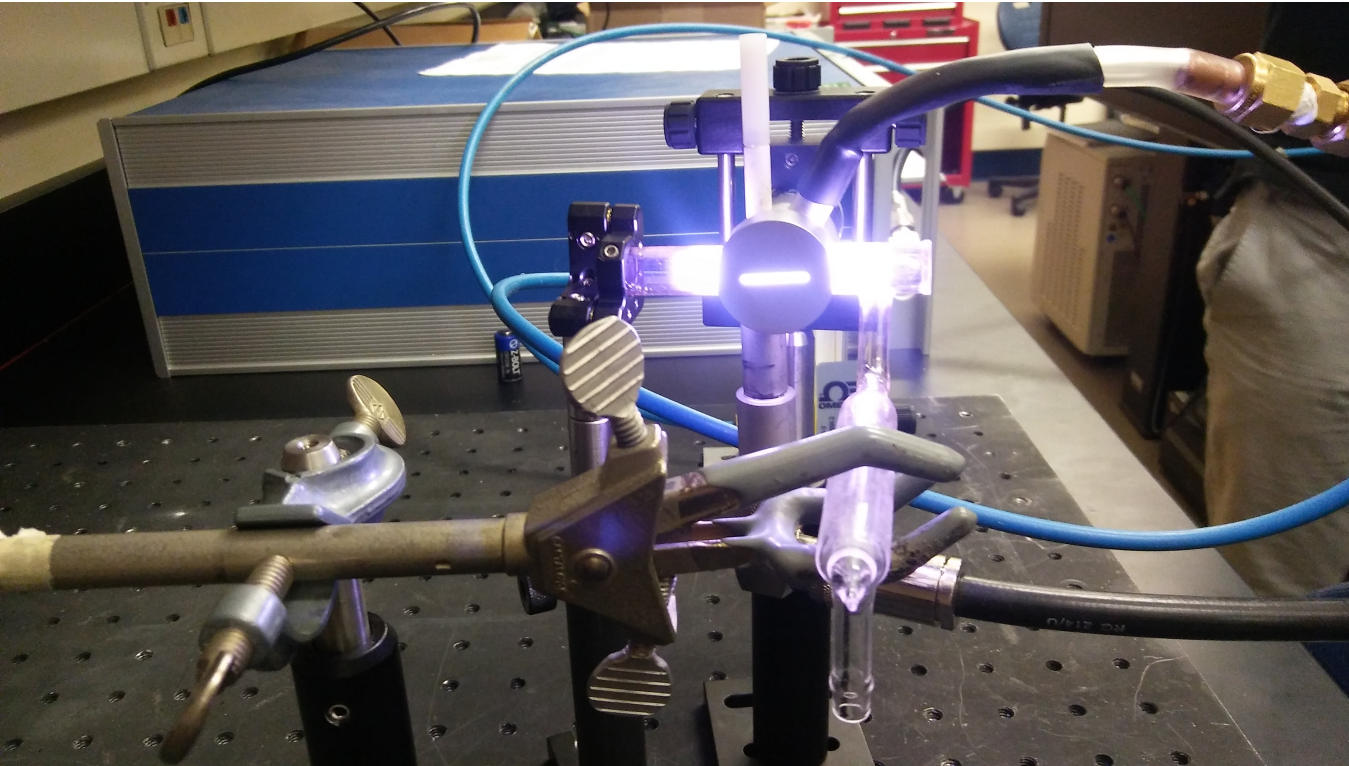
CURRENT PROJECTS – TWO PHOTON FLUORESCENCE



CURRENT PROJECTS – MOTH OLFACTORY SYSTEMS

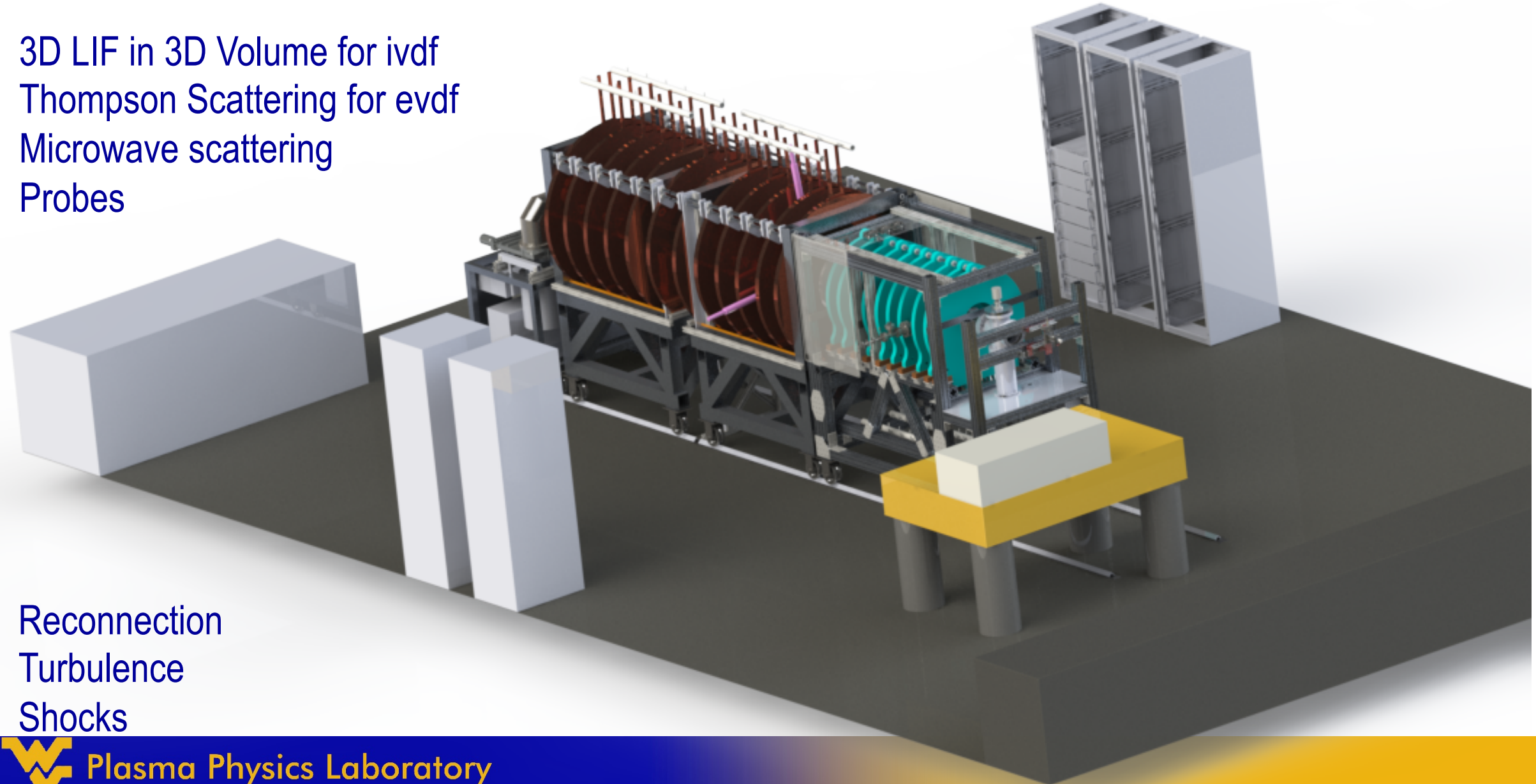


CURRENT PROJECTS – IODINE ELECTRIC PROPULSION



PHASE SPACE MEASUREMENTS (PHASMA)

3D LIF in 3D Volume for ivdf
Thompson Scattering for evdf
Microwave scattering
Probes



Reconnection
Turbulence
Shocks



Acknowledgements

- Scime Group:
Dr. Derek Thompson, Thomas Steinberger, John McKee, Miguel Henriquez, Jacob McLaughlin, Andrew Jemiolo, Dr. Earl Scime
- Arturo Dominguez



References

Figure 2: By Author: ourworldindata.org - Original text : Data source:

https://en.wikipedia.org/wiki/Transistor_countURL: <https://ourworldindata.org/wp-content/uploads/2013/05/Transistor-Count-over-time.png>Article: [https://ourworldindata.org/technological progress](https://ourworldindata.org/technological-progress)), CC BY-SA 4.0, <https://commons.wikimedia.org/w/index.php?curid=71553709>

Figure 3: Davide Sacchetto, Design Aspects of Carry Lookahead Adders with Vertically-Stacked Nanowire Transistors

Figure 4: By German Wikipediabiatch, original upload 7. Okt 2004 by Stahlkocher de:Bild:Wafer 2 Zoll bis 8Zoll.jpg, CC BY-SA 3.<https://commons.wikimedia.org/w/index.php?curid=928106>

